

forming a first conductive layer of a material which is substantially unetchable by chemical dry-etching;

forming a second conductive layer on the first conductive layer from a material which is etchable by chemical dry-etching;

structuring the second conductive layer to form a structured second layer; and

dry etching the first conductive layer while using the second structured layer as a mask.

u² Claim 8 (amended). The method according to claim 1, further comprising:

applying at least one insulation layer on the electrode configuration, and structuring the insulation layer to form at least one contact hole to the electrode configuration; and

depositing a conductive layer and filling in the contact hole.

u³ Claim 14 (amended). The method according to claim 1, further comprising chemical dry etching the second conductive layer while using the first structured layer as a barrier for the chemical dry-etching.

Enter The Following New Claims:

-- 21. The method according to claim 1, wherein the material for forming the first conductive layer is selected from the group consisting of a 4d transition metal, a 5d transition metal, a conductive nitride thereof, and a conductive oxide thereof.

22. The method according to claim 1, wherein the material for forming the first conductive layer is selected from the group of platinum metals. --